metal-organic papers

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Key indicators

Single-crystal X-ray study T = 294 K Mean σ (C–C) = 0.005 Å R factor = 0.035 wR factor = 0.079 Data-to-parameter ratio = 18.0

For details of how these key indicators were automatically derived from the article, see http://journals.iucr.org/e. The arsenic(V) compound PhAs(O)(OH)(OSiPh₃)

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The structure of the arsenosilicate compound, hydroxooxo-(phenyl)(triphenylsiloxy)arsenic(V), PhAs(O)(OH)(OSiPh₃) or [As(C₆H₅)(C₁₈H₁₅OSi)O(OH)], is dimeric with the monomers joined by two As $-O-H\cdots O$ =As hydrogen-bonding sequences about an inversion centre, with $O\cdots O = 2.528$ (3) Å. The monomer unit has a tetrahedral AsO₃C_{Ph} entity. The As-O-Si angle [140.79 (12)°] is larger than any previously reported As^V-O-Si angle in a molecular species. The three independent As-O bond lengths are 1.6551 (18), 1.6740 (18) and 1.7086 (17) Å, respectively, for the As=O, As-OH and As $-OSiPh_3$ bonds.

Comment

The small number of molecular silvlarsenates, *i.e.* arsenic(V) silicates, which have been structurally characterized all contain terminal As^V-OSiMe₃ units (Baier et al., 1992, 1993*a*,*b*). The compounds are the silvlated aminoarsenates (Me₃SiO)₂(PhNH)AsO, (I), and (Me₃SiO)₃AsO(Me₃SiO)₃-AsNMe, (II), a triarsa(V)azene compound, [(Me₃SiO)₂AsN]₃, (III), and a diarsenate(V) compound, (Me₃SiO)₈As₄O₆, (IV). Compounds (I) and (III) contain four-coordinate arsenic, (II) has five-coordinate arsenic and (IV) contains arsenic in both four- and six-coordination. Only in (Me₃SiO)₂(PhNH)-AsO, (I), is there an As=O bond present (Baier *et al.*, 1993b). In an attempt to prepare $PhAs(O)(OSiPh_3)_2$ via a dehydration reaction, phenylarsonic acid was reacted with triphenylsilanol in a 1:2 molar ratio (O'Leary, 1998). The reaction did not proceed as anticipated and successive crystallizations from a dichloromethane-ether-cyclohexane (1:1:4) solution afforded what we subsequently established to be the title compound PhAs(O)(OH)(OSiPh₃), (V), and Ph₃SiOSiPh₃. When the reaction was repeated using a 1:1 molar ratio of phenylarsonic acid to triphenylsilanol, compound (V) was the only product obtained.



A search of the December 2003 release of the Cambridge Structural Database (Allen, 2002) shows that compound (V) is indeed a novel species and is the first structurally characterized silylarsenate containing both As-OSi and As-OH units. In the solid state, the structure is dimeric as shown in (V) with the monomers joined by two $As-O-H\cdots O=As$ hydrogen-bonding sequences about an inversion centre

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Figure 1

A view of the dimer of (V) with the atomic numbering scheme. Displacement ellipsoids are drawn at the 30% probability level. Atom labels with suffix 'a' represent the equivalent position (1 - x, 1 - y), 1 - z).

(Fig. 1). The monomers contain a central tetrahedral AsO_3C_{Ph} unit bound through one of the O atoms to a tetrahedral -SiPh₃ group. Principal bond-length and angle data for (V) are given in Table 1.

The As-O-Si angle in (V) $[140.79 (12)^{\circ}]$ is larger than any previously reported As^V–O–Si angles, which range from 128.5 (4) to 136.0 (3)° (Baier *et al.*, 1992, 1993*a*,*b*). The As^V- O_{si} distance in (V) [1.7086 (17) Å] lies within the range of the corresponding distances in the previously reported As^Vcontaining compounds (I)-(IV) [1.680 (3)-1.780 (2) Å]. The As^{III}-O_{Si} distances in PhAs(OSiPh₃)₂, (VI) (Ferguson et al., 2004), are 1.758 (3) and 1.786 (3) Å, and are significantly longer than the $As^{V} - O_{Si}$ distance in (V).

As expected, the As-OH bond in (V) [1.6740 (18) Å] is significantly shorter than the As $-O_{Si}$ bond [1.7086 (17) Å]. The As=O double bond in (V) [1.6551 (18) Å] is close to the value of the As-OH single bond and longer than the As=O distance of 1.626 (3) Å in the N-H···O hydrogen-bonded system (Me₃SiO)₂(PhNH)AsO, (I) (Baier et al., 1993b). A mean value of 1.661 Å has been suggested for the As=O distance (Allen et al., 1987).

The Si $-O_{As}$ distance in (V) [1.6585 (18) Å] is not unusual. Comparable distances in (Me₃SiO)₃AsO(Me₃SiO)₃AsNMe, (II), and $[(Me_3SiO)_2AsN]_3$, (III), range from 1.646 (2) to 1.732 (6) Å. The Si $-O_{As}$ distances in PhAs(OSiPh₃)₂, (VI) (Ferguson et al., 2004), are 1.635 (3) and 1.641 (4) Å, and are shorter than the Si $-O_{As}$ distance in (V). The As $-C_{Ph}$ bond length in (V) [1.891 (3) Å] is relatively short, since a mean value of 1.922 Å has been suggested for $As-C_{ar}$ bonds in general, where the As atom is four-coordinate and Car is a C atom in an aromatic system (Allen *et al.*, 1987). The As $-C_{ar}$ distance in PhAs(OSiPh₃)₂, (VI) (Ferguson et al., 2004), of 1.936 (5) A is significantly greater than the distance of 1.891 (3) Å in (V). The Si-C and C-C distances in the SiPh₃ units of (V) are normal.

The two O-As=O angles in (V), viz. O1-As1-O2 and O2-As1-O3 in Fig. 1, are 110.76 (10) and 114.05 (10)°, and

do not agree within 3 s.u.; the O1-As1-O3 angle is notably smaller at 103.11 (10)°. The three O-Si-C angles in (V) lie between 103.41 (11) and 110.96 (11) $^{\circ}$, whilst the range for the three C-Si-C angles is 110.40 (12)-111.37 (12) $^{\circ}$.

The AsO-H···O=As hydrogen-bond data for (V) (Table 2) indicate the presence of moderately strong hydrogen bonding (Jeffrey, 1997). The hydrogen-bonding pattern is similar to that in (I), (Me₃SiO)₂(PhNH)AsO. Like (V), the structure of (I) is dimeric, with the monomers connected via two AsN-H···O=As hydrogen bonds, but unlike (V), the monomers in (I) are not symmetry-related (Baier et al., 1993b). As expected, all phenyl rings take part in C-H··· π interactions (Table 2) with phenyl rings of adjacent molecules to generate a three-dimensional network.

Experimental

For the synthesis of PhAs(O)(OH)(OSiPh₃), (V), phenylarsonic acid (2.009 g, 9.94 mmol) and triphenylsilanol (2.747 g, 9.94 mmol) were added to 50 ml toluene in a Dean-Stark apparatus. The solution was heated at reflux for 10 h. Removal of toluene afforded a colourless solid which was crystallized from dichloromethane-heptane (1:3) to give crystals of (V) (3.625 g, 79.2%; m.p. 436-438 K). Found: C 62.9, H 4.9%; C₂₄H₂₁AsO₃Si requires: C 62.6, H 4.6%. FT-IR (KBr disc), $v_{\text{max}} \text{ cm}^{-1}$: 1428 (s), 1119 (s), 956 (s), 910 (vs), 714 (s), 699 (s), 508 (vs). ¹H NMR (270 MHz, CDCl₃, p.p.m.): 8.95 (s, 2H, OH), 7.49–7.03 (m, 40H, C₆H₅As and C₆H₅Si). ¹³C NMR (CDCl₃, p.p.m.): 151.05; 136.22, 135.41, 131.00, 129.99, 129.27, 128.49, 127.49 (SiC₆H₅ and AsC₆H₅). EIMS m/z [M = monomeric unit [PhAs(O)(OH)(OSiPh₃)]: 460 [M], 383 [*M* – Ph], 306 [*M* – 2Ph], 275 [Ph₃SiO].

Crybrar adam	Crystal	data
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[As(C ₆ H ₅)(C ₁₈ H ₁₅ OSi)O(OH)]	Z = 2
$M_r = 460.42$	$D_x = 1.413 \text{ Mg m}^{-3}$
Triclinic, $P\overline{1}$	Mo K α radiation
a = 8.3350 (9) Å	Cell parameters from 25
b = 9.8193 (8) Å	reflections
c = 14.8736 (14) Å	$\theta = 14.6 - 21.6^{\circ}$
$\alpha = 89.948 \ (6)^{\circ}$	$\mu = 1.65 \text{ mm}^{-1}$
$\beta = 74.391 \ (9)^{\circ}$	T = 294 (1) K
$\gamma = 68.276 \ (5)^{\circ}$	Lath, colourless
$V = 1082.51 (18) \text{ Å}^3$	$0.42 \times 0.38 \times 0.22 \text{ mm}$

Data collection

3281 reflections with $I > 2\sigma(I)$
$\theta_{\rm max} = 27.0^{\circ}$
$h = -10 \rightarrow 9$
$k = 0 \rightarrow 12$
$l = -18 \rightarrow 19$
3 standard reflections
frequency: 120 min
intensity decay: none

Refinement

Refinement on F^2 $R[F^2 > 2\sigma(F^2)] = 0.035$ $wR(F^2) = 0.080$ S = 1.014751 reflections 264 parameters H-atom parameters constrained

 $w = 1/[\sigma^2(F_o^2) + (0.0386P)^2]$ + 0.0624P] where $P = (F_o^2 + 2F_c^2)/3$ $(\Delta/\sigma)_{\rm max} = 0.002$ $\Delta \rho_{\rm max} = 0.30 \text{ e } \text{\AA}^{-3}$ $\Delta \rho_{\rm min} = -0.32 \text{ e } \text{\AA}^{-3}$ Extinction correction: SHELXL97 Extinction coefficient: 0.0044 (9)

Table 1

Selected	geometric	parameters	(A,	°).
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As1-O1	1.7086 (17)	Si1-O1	1.6585 (18)
As1-O2	1.6551 (18)	Si1-C21	1.860 (3)
As1-O3	1.6740 (18)	Si1-C31	1.857 (3)
As1-C11	1.891 (3)	Si1-C41	1.862 (3)
O2-As1-O3	114.05 (10)	O1-Si1-C21	103.41 (11)
O2-As1-O1	110.76 (10)	C31-Si1-C21	111.04 (11)
O3-As1-O1	103.12 (10)	O1-Si1-C41	110.96 (11)
O2-As1-C11	111.69 (12)	C31-Si1-C41	110.40 (12)
O3-As1-C11	110.74 (12)	C21-Si1-C41	111.37 (12)
O1-As1-C11	105.85 (11)	Si1-O1-As1	140.79 (12)
O1-Si1-C31	109.47 (11)		

Table 2

Hydrogen-bonding and short-contact geometry (Å, °).

$\overline{D-\mathrm{H}\cdots A}$	$D-\mathrm{H}$	$H \cdot \cdot \cdot A$	$D \cdots A$	$D - \mathbf{H} \cdot \cdot \cdot A$
$\overline{O3-H3\cdots O2^{i}}$	0.82	1.73	2.528 (3)	164
$C15-H15\cdots Cg2^{ii}$	0.93	2.85	3.536	132
$C24-H24\cdots Cg4^{iii}$	0.93	3.04	3.932	160
$C33-H33\cdots Cg4^{ii}$	0.93	2.96	3.784	149
$C35-H35\cdots Cg2^{iv}$	0.93	3.01	3.824	147
$C42-H42\cdots Cg1^{v}$	0.93	3.14	3.946	146

Symmetry codes: (i) 1-x, 1-y, 1-z; (ii) x-1, y, z; (iii) x, 1+y, z; (iv) 1-x, 2-y, -z; (v) 1+x, y, z. Cg1 to Cg4 are the centroids of the phenyl rings Cn1-Cn6 (n = 1-4), respectively.

Peaks consistent with the H atoms were visible in difference maps and all H atoms were subsequently included as riding atoms, with O– H = 0.82 Å and $U_{iso}(H) = 1.5U_{eq}(O)$, and C–H = 0.93 Å and $U_{iso}(H)$ = $1.2U_{eq}(C)$. Data collection: *CAD-4-PC Software* (Enraf–Nonius, 1992); cell refinement: *SET4* and *CELDIM* (Enraf–Nonius, 1992); data reduction: *DATRD2* in *NRCVAX94* (Gabe *et al.*, 1989); program(s) used to solve structure: *NRCVAX94 via* Patterson heavy-atom method; program(s) used to refine structure: *SHELXL97* (Sheldrick, 1997) and *WinGX* (Farrugia, 1999); molecular graphics: *ORTEPII* (Johnson, 1976) and *PLATON* (Spek, 2003); software used to prepare material for publication: *SHELXL97*.

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